Listing of the Claims:

Please cancel claims 1-45.

46. (New) A method of making an interposer, comprising:

forming an oxide layer on each of a first surface and a second surface of a substrate;

patterning the oxide layer of the first surface to expose a first portion and a second portion of the substrate;

isotropically etching through the first portion of the exposed substrate to form a first portion of at least one deep-via opening;

anisotropically etching through the second portion of the exposed substrate to form a second portion of the at least one deep-via opening;

sputtering a copper barrier layer and a copper seed layer into the first and second portions of the at least one deep-via opening;

electroplating a conductive material over the seed layer to form the at least one deep-via; and

forming vias and interconnect lines over the second surface of the substrate.

- 47. (New) The method of claim 46 wherein the interconnect lines are electrically coupled to the at least one deep-via.
- 48. (New) The method of claim 46 wherein the oxide layer is thermally grown to a thickness of approximately 0.5μ .

- 49. (New) The method of claim 46 further growing an oxide layer on inner surfaces of the at least deep-via opening prior to the sputtering the copper barrier and the copper seed layer.
- 50. (New) The method of claim 46 wherein the copper barrier layer is of a thickness in a range of 10-50 nm.
- 51. (New) The method of claim 46 wherein the copper seed layer layer is of a thickness in a range of 100-300 nm.
- 52. (New) The method of claim 46 further comprising depositing a copper layer over the first surface of the substrate.
- 53. (New) The method of claim 46 further comprising:

forming a silicon nitride layer over the second surface of the substrate; depositing an oxide layer superjacent to the silicon nitride layer; patterning the oxide layer to expose portions of the silicon nitride layer; etching the exposed portions of the silicon nitride layer;

depositing a copper barrier layer and a copper seed layer over the second surface of the substrate; and

electroplating a conductive material over the copper seed layer.

54. (New) A method of making an interposer comprising:

forming a first set of interconnect lines over a first surface of a substrate;

forming a second set of interconnect lines over the first surface of the substrate; and

forming vias between the first set of interconnect lines and the second set of interconnect lines, wherein the vias are formed with slopped sidewalls, the method further comprising:

forming a first oxide layer on a first surface of a substrate and a second oxide layer on a second surface of the substrate;

forming a first silicon nitride layer superjacent to the first oxide layer; patterning the first silicon nitride layer to expose portions of the first silicon nitride layer;

etching the exposed portions of the first silicon nitride layer to form trenches;

sputtering a copper barrier layer and a copper seed layer over the first surface of the substrate;

electroplating a conductive material over the copper seed layer;
forming interconnect lines over the first surface of the substrate; and
depositing a second silicon nitride layer over the first surface of the substrate.

55. (New) The method of claim 55 further comprising:

patterning the second oxide layer to expose portions of the second oxide layer to be removed to form a deep-via opening with slopped sidewalls;

etching the exposed portions of the second oxide layer to form the deepvia opening;

sputtering a copper barrier layer and a copper seed layer into the deep-via opening; and

4

electroplating a conductive material over the copper seed layer.